



**America Semiconductor**

**Silicon Bridge Rectifier**

**BR605 thru  
BR64**

**$V_{RRM} = 50\text{ V} - 1000\text{ V}$**

**$I_F = 6\text{ A}$**

**Features**

- Types up to 1000 V  $V_{RRM}$
- Ideal for printed circuit board
- Low forward voltage drop
- High temperature soldering guaranteed: 250°C/ 10 seconds, 0.375" lead length
- Low leakage current

**BR-6 Package**



**Mechanical Data**

Case: Molded plastic body  
Polarity: Marked on body  
Mounting position: Any  
Mounting: Hole for number 6 screw

**Maximum ratings, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	BR605	BR61	BR62	BR64	Unit
Repetitive peak reverse voltage	$V_{RRM}$		50	100	200	400	V
RMS reverse voltage	$V_{RMS}$		35	70	140	280	V
DC blocking voltage	$V_{DC}$		50	100	200	400	V
Continuous forward current	$I_F$	$T_C \leq 75\text{ °C}$	6	6	6	6	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	125	125	125	125	A
Operating temperature	$T_j$		-65 to 125	-65 to 125	-65 to 125	-65 to 125	°C
Storage temperature	$T_{stg}$		-65 to 150	-65 to 150	-65 to 150	-65 to 150	°C

**Electrical characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	BR605	BR61	BR62	BR64	Unit
Diode forward voltage	$V_F$	$I_F = 3\text{ A}$ , $T_j = 25\text{ °C}$	1	1	1	1	V
Reverse current	$I_R$	$V_R = 50\text{ V}$ , $T_j = 25\text{ °C}$	10	10	10	10	$\mu\text{A}$
		$V_R = 50\text{ V}$ , $T_j = 100\text{ °C}$	200	200	200	200	





FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

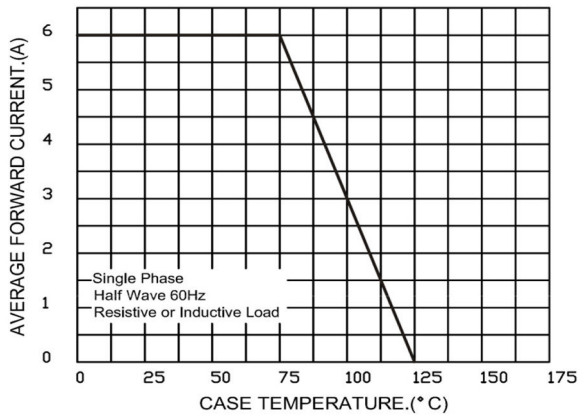


FIG.2-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

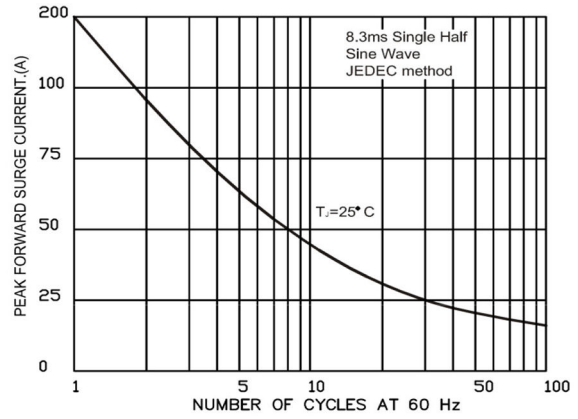


FIG.3-TYPICAL FORWARD CHARACTERISTICS

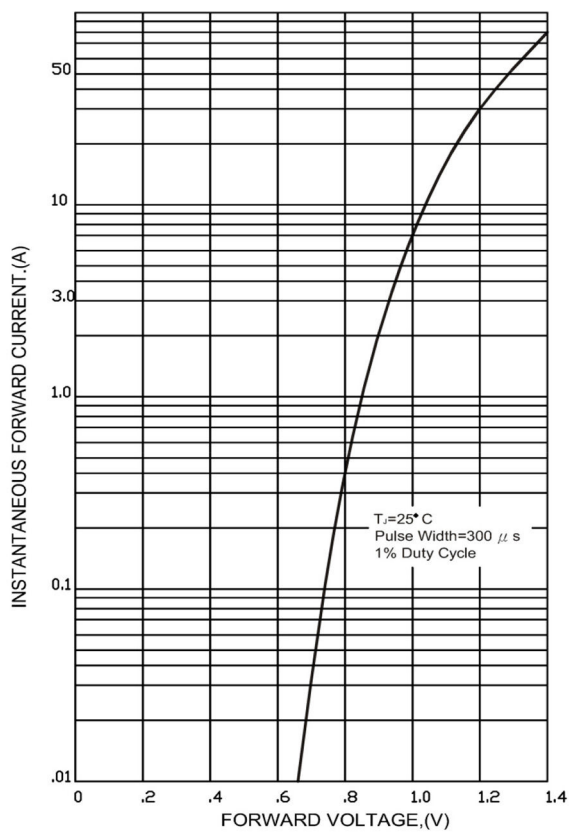


FIG.4-TYPICAL REVERSE CHARACTERISTICS

